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## Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

## Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

### Details

Product Status	Active
Number of LABs/CLBs	8375
Number of Logic Elements/Cells	67000
Total RAM Bits	4526080
Number of I/O	295
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	484-BBGA
Supplier Device Package	484-FPBGA (23x23)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe3-70ea-6fn484c">https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe3-70ea-6fn484c</a>

**Figure 2-4. General Purpose PLL Diagram**

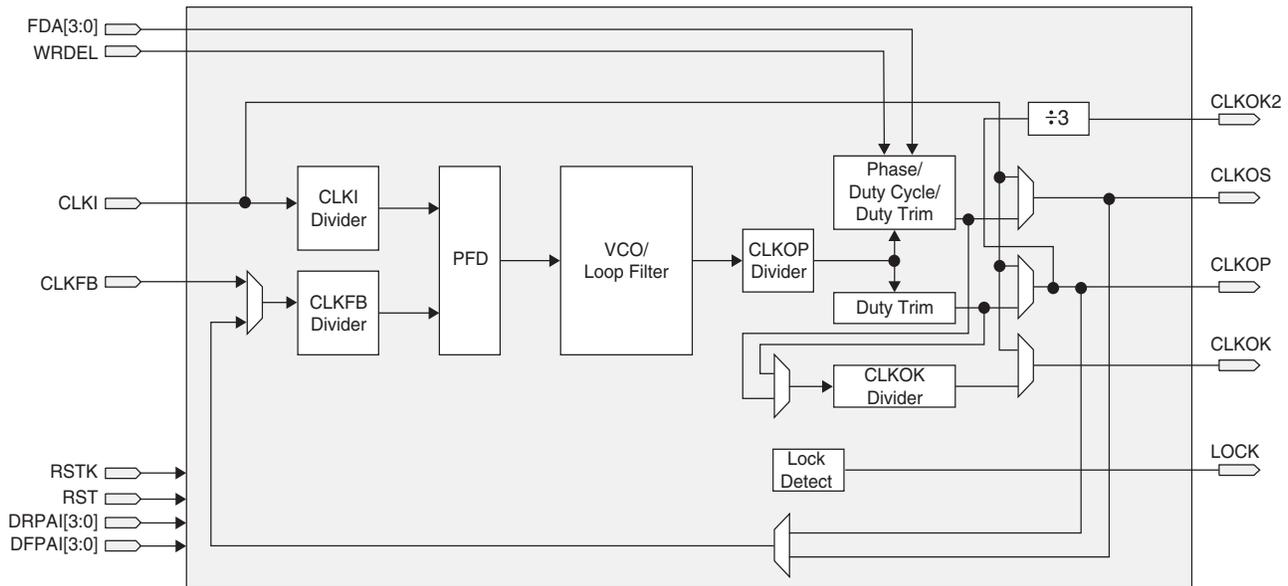


Table 2-4 provides a description of the signals in the PLL blocks.

**Table 2-4. PLL Blocks Signal Descriptions**

Signal	I/O	Description
CLKI	I	Clock input from external pin or routing
CLKFB	I	PLL feedback input from CLKOP, CLKOS, or from a user clock (pin or logic)
RST	I	"1" to reset PLL counters, VCO, charge pumps and M-dividers
RSTK	I	"1" to reset K-divider
WRDEL	I	DPA Fine Delay Adjust input
CLKOS	O	PLL output to clock tree (phase shifted/duty cycle changed)
CLKOP	O	PLL output to clock tree (no phase shift)
CLKKOK	O	PLL output to clock tree through secondary clock divider
CLKKOK2	O	PLL output to clock tree (CLKOP divided by 3)
LOCK	O	"1" indicates PLL LOCK to CLKI
FDA [3:0]	I	Dynamic fine delay adjustment on CLKOS output
DRPAI[3:0]	I	Dynamic coarse phase shift, rising edge setting
DFPAI[3:0]	I	Dynamic coarse phase shift, falling edge setting

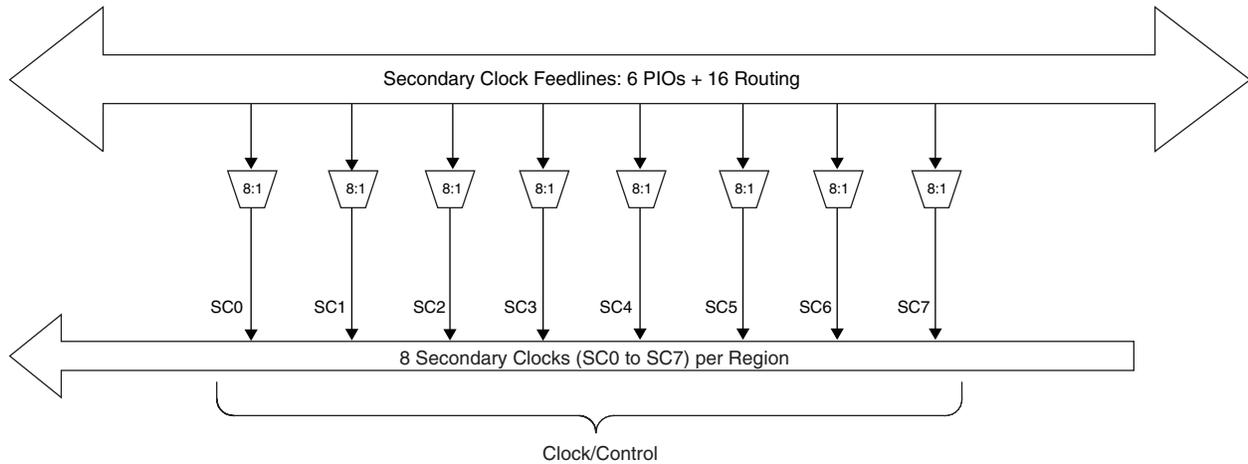
### Delay Locked Loops (DLL)

In addition to PLLs, the LatticeECP3 family of devices has two DLLs per device.

CLKI is the input frequency (generated either from the pin or routing) for the DLL. CLKI feeds into the output muxes block to bypass the DLL, directly to the DELAY CHAIN block and (directly or through divider circuit) to the reference input of the Phase Detector (PD) input mux. The reference signal for the PD can also be generated from the Delay Chain signals. The feedback input to the PD is generated from the CLKFB pin or from a tapped signal from the Delay chain.

The PD produces a binary number proportional to the phase and frequency difference between the reference and feedback signals. Based on these inputs, the ALU determines the correct digital control codes to send to the delay

**Figure 2-16. Per Region Secondary Clock Selection**

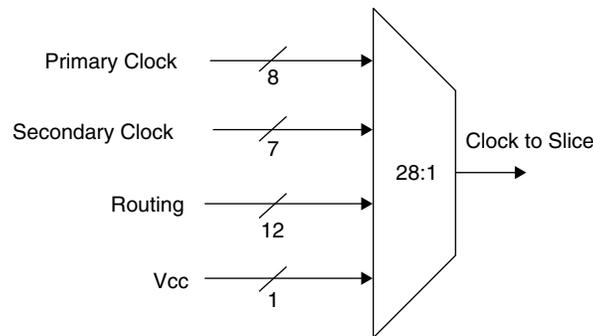


**Slice Clock Selection**

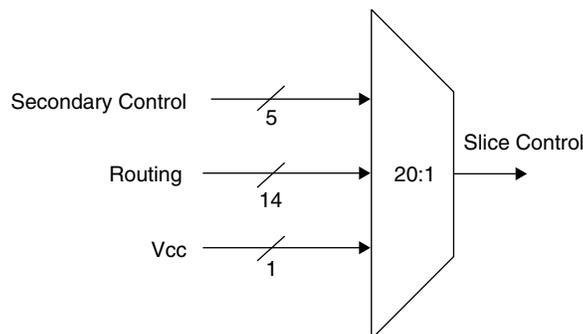
Figure 2-17 shows the clock selections and Figure 2-18 shows the control selections for Slice0 through Slice2. All the primary clocks and seven secondary clocks are routed to this clock selection mux. Other signals can be used as a clock input to the slices via routing. Slice controls are generated from the secondary clocks/controls or other signals connected via routing.

If none of the signals are selected for both clock and control then the default value of the mux output is 1. Slice 3 does not have any registers; therefore it does not have the clock or control muxes.

**Figure 2-17. Slice0 through Slice2 Clock Selection**



**Figure 2-18. Slice0 through Slice2 Control Selection**



Two adjacent PIOs can be joined to provide a differential I/O pair (labeled as “T” and “C”) as shown in Figure 2-32. The PAD Labels “T” and “C” distinguish the two PIOs. Approximately 50% of the PIO pairs on the left and right edges of the device can be configured as true LVDS outputs. All I/O pairs can operate as LVDS inputs.

**Table 2-11. PIO Signal List**

Name	Type	Description
INDD	Input Data	Register bypassed input. This is not the same port as INCK.
IPA, INA, IPB, INB	Input Data	Ports to core for input data
OPOSA, ONEGA <sup>1</sup> , OPOSB, ONEGB <sup>1</sup>	Output Data	Output signals from core. An exception is the ONEGB port, used for tristate logic at the DQS pad.
CE	PIO Control	Clock enables for input and output block flip-flops.
SCLK	PIO Control	System Clock (PCLK) for input and output/TS blocks. Connected from clock ISB.
LSR	PIO Control	Local Set/Reset
ECLK1, ECLK2	PIO Control	Edge clock sources. Entire PIO selects one of two sources using mux.
ECLKDQSR <sup>1</sup>	Read Control	From DQS_STROBE, shifted strobe for memory interfaces only.
DDRCLKPOL <sup>1</sup>	Read Control	Ensures transfer from DQS domain to SCLK domain.
DDRLAT <sup>1</sup>	Read Control	Used to guarantee INDDR2 gearing by selectively enabling a D-Flip-Flop in datapath.
DEL[3:0]	Read Control	Dynamic input delay control bits.
INCK	To Clock Distribution and PLL	PIO treated as clock PIO, path to distribute to primary clocks and PLL.
TS	Tristate Data	Tristate signal from core (SDR)
DQCLK0 <sup>1</sup> , DQCLK1 <sup>1</sup>	Write Control	Two clocks edges, 90 degrees out of phase, used in output gearing.
DQSW <sup>2</sup>	Write Control	Used for output and tristate logic at DQS only.
DYNDEL[7:0]	Write Control	Shifting of write clocks for specific DQS group, using 6:0 each step is approximately 25ps, 128 steps. Bit 7 is an invert (timing depends on input frequency). There is also a static control for this 8-bit setting, enabled with a memory cell.
DCNTL[6:0]	PIO Control	Original delay code from DDR DLL
DATAVALID <sup>1</sup>	Output Data	Status flag from DATAVALID logic, used to indicate when input data is captured in IOLOGIC and valid to core.
READ	For DQS_Strobe	Read signal for DDR memory interface
DQSI	For DQS_Strobe	Unshifted DQS strobe from input pad
PRMBDET	For DQS_Strobe	DQSI biased to go high when DQSI is tristate, goes to input logic block as well as core logic.
GSRN	Control from routing	Global Set/Reset

1. Signals available on left/right/top edges only.

2. Selected PIO.

## PIO

The PIO contains four blocks: an input register block, output register block, tristate register block and a control logic block. These blocks contain registers for operating in a variety of modes along with the necessary clock and selection logic.

### Input Register Block

The input register blocks for the PIOs, in the left, right and top edges, contain delay elements and registers that can be used to condition high-speed interface signals, such as DDR memory interfaces and source synchronous interfaces, before they are passed to the device core. Figure 2-33 shows the input register block for the left, right and top edges. The input register block for the bottom edge contains one element to register the input signal and no DDR registers. The following description applies to the input register block for PIOs in the left, right and top edges only.

## Control Logic Block

The control logic block allows the selection and modification of control signals for use in the PIO block.

## DDR Memory Support

Certain PICs have additional circuitry to allow the implementation of high-speed source synchronous and DDR, DDR2 and DDR3 memory interfaces. The support varies by the edge of the device as detailed below.

### Left and Right Edges

The left and right sides of the PIC have fully functional elements supporting DDR, DDR2, and DDR3 memory interfaces. One of every 12 PIOs supports the dedicated DQS pins with the DQS control logic block. Figure 2-35 shows the DQS bus spanning 11 I/O pins. Two of every 12 PIOs support the dedicated DQS and DQS# pins with the DQS control logic block.

### Bottom Edge

PICs on the bottom edge of the device do not support DDR memory and Generic DDR interfaces.

### Top Edge

PICs on the top side are similar to the PIO elements on the left and right sides but do not support gearing on the output registers. Hence, the modes to support output/tristate DDR3 memory are removed on the top side.

The exact DQS pins are shown in a dual function in the Logic Signal Connections table in this data sheet. Additional detail is provided in the Signal Descriptions table. The DQS signal from the bus is used to strobe the DDR data from the memory into input register blocks. Interfaces on the left, right and top edges are designed for DDR memories that support 10 bits of data.

**Figure 2-35. DQS Grouping on the Left, Right and Top Edges**

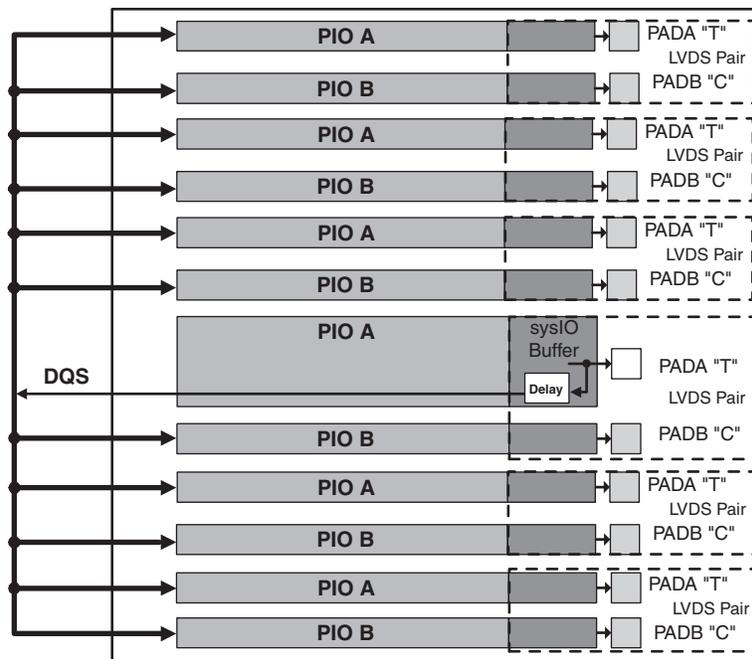
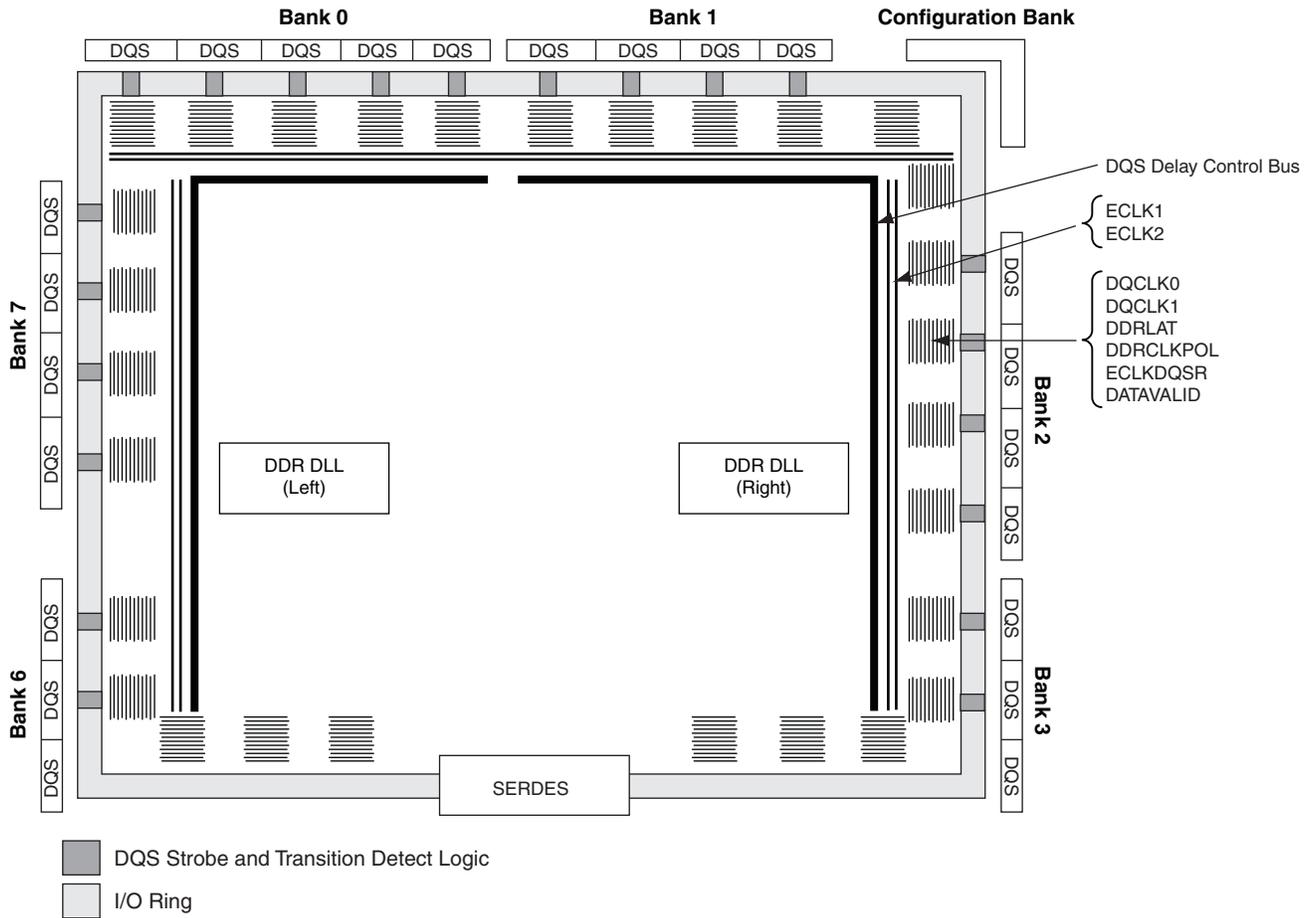


Figure 2-36. Edge Clock, DLL Calibration and DQS Local Bus Distribution



\*Includes shared configuration I/Os and dedicated configuration I/Os.

To accomplish write leveling in DDR3, each DQS group has a slightly different delay that is set by DYN DELAY[7:0] in the DQS Write Control logic block. The DYN DELAY can set 128 possible delay step settings. In addition, the most significant bit will invert the clock for a 180-degree shift of the incoming clock.

LatticeECP3 input and output registers can also support DDR gearing that is used to receive and transmit the high speed DDR data from and to the DDR3 Memory.

LatticeECP3 supports the 1.5V SSTL I/O standard required for the DDR3 memory interface. For more information, refer to the sysIO section of this data sheet.

Please see TN1180, [LatticeECP3 High-Speed I/O Interface](#) for more information on DDR Memory interface implementation in LatticeECP3.

## sysI/O Buffer

Each I/O is associated with a flexible buffer referred to as a sysI/O buffer. These buffers are arranged around the periphery of the device in groups referred to as banks. The sysI/O buffers allow users to implement the wide variety of standards that are found in today's systems including LVDS, BLVDS, HSTL, SSTL Class I & II, LVCMOS, LVTTL, LVPECL, PCI.

### sysI/O Buffer Banks

LatticeECP3 devices have six sysI/O buffer banks: six banks for user I/Os arranged two per side. The banks on the bottom side are wraparounds of the banks on the lower right and left sides. The seventh sysI/O buffer bank (Configuration Bank) is located adjacent to Bank 2 and has dedicated/shared I/Os for configuration. When a shared pin is not used for configuration it is available as a user I/O. Each bank is capable of supporting multiple I/O standards. Each sysI/O bank has its own I/O supply voltage ( $V_{CCIO}$ ). In addition, each bank, except the Configuration Bank, has voltage references,  $V_{REF1}$  and  $V_{REF2}$ , which allow it to be completely independent from the others. Figure 2-38 shows the seven banks and their associated supplies.

In LatticeECP3 devices, single-ended output buffers and ratioed input buffers (LVTTL, LVCMOS and PCI) are powered using  $V_{CCIO}$ . LVTTL, LVCMOS33, LVCMOS25 and LVCMOS12 can also be set as fixed threshold inputs independent of  $V_{CCIO}$ .

Each bank can support up to two separate  $V_{REF}$  voltages,  $V_{REF1}$  and  $V_{REF2}$ , that set the threshold for the referenced input buffers. Some dedicated I/O pins in a bank can be configured to be a reference voltage supply pin. Each I/O is individually configurable based on the bank's supply and reference voltages.

### SCI (SERDES Client Interface) Bus

The SERDES Client Interface (SCI) is an IP interface that allows the SERDES/PCS Quad block to be controlled by registers rather than the configuration memory cells. It is a simple register configuration interface that allows SERDES/PCS configuration without power cycling the device.

The Diamond and ispLEVER design tools support all modes of the PCS. Most modes are dedicated to applications associated with a specific industry standard data protocol. Other more general purpose modes allow users to define their own operation. With these tools, the user can define the mode for each quad in a design.

Popular standards such as 10Gb Ethernet, x4 PCI Express and 4x Serial RapidIO can be implemented using IP (available through Lattice), a single quad (Four SERDES channels and PCS) and some additional logic from the core.

The LatticeECP3 family also supports a wide range of primary and secondary protocols. Within the same quad, the LatticeECP3 family can support mixed protocols with semi-independent clocking as long as the required clock frequencies are integer x1, x2, or x11 multiples of each other. Table 2-15 lists the allowable combination of primary and secondary protocol combinations.

### Flexible Quad SERDES Architecture

The LatticeECP3 family SERDES architecture is a quad-based architecture. For most SERDES settings and standards, the whole quad (consisting of four SERDES) is treated as a unit. This helps in silicon area savings, better utilization and overall lower cost.

However, for some specific standards, the LatticeECP3 quad architecture provides flexibility; more than one standard can be supported within the same quad.

Table 2-15 shows the standards can be mixed and matched within the same quad. In general, the SERDES standards whose nominal data rates are either the same or a defined subset of each other, can be supported within the same quad. In Table 2-15, the Primary Protocol column refers to the standard that determines the reference clock and PLL settings. The Secondary Protocol column shows the other standard that can be supported within the same quad.

Furthermore, Table 2-15 also implies that more than two standards in the same quad can be supported, as long as they conform to the data rate and reference clock requirements. For example, a quad may contain PCI Express 1.1, SGMII, Serial RapidIO Type I and Serial RapidIO Type II, all in the same quad.

**Table 2-15. LatticeECP3 Primary and Secondary Protocol Support**

Primary Protocol	Secondary Protocol
PCI Express 1.1	SGMII
PCI Express 1.1	Gigabit Ethernet
PCI Express 1.1	Serial RapidIO Type I
PCI Express 1.1	Serial RapidIO Type II
Serial RapidIO Type I	SGMII
Serial RapidIO Type I	Gigabit Ethernet
Serial RapidIO Type II	SGMII
Serial RapidIO Type II	Gigabit Ethernet
Serial RapidIO Type II	Serial RapidIO Type I
CPRI-3	CPRI-2 and CPRI-1
3G-SDI	HD-SDI and SD-SDI

### sysI/O Single-Ended DC Electrical Characteristics

Input/Output Standard	$V_{IL}$		$V_{IH}$		$V_{OL}$ Max. (V)	$V_{OH}$ Min. (V)	$I_{OL}^1$ (mA)	$I_{OH}^1$ (mA)
	Min. (V)	Max. (V)	Min. (V)	Max. (V)				
LVCMOS33	-0.3	0.8	2.0	3.6	0.4	$V_{CCIO} - 0.4$	20, 16, 12, 8, 4	-20, -16, -12, -8, -4
					0.2	$V_{CCIO} - 0.2$	0.1	-0.1
LVCMOS25	-0.3	0.7	1.7	3.6	0.4	$V_{CCIO} - 0.4$	20, 16, 12, 8, 4	-20, -16, -12, -8, -4
					0.2	$V_{CCIO} - 0.2$	0.1	-0.1
LVCMOS18	-0.3	$0.35 V_{CCIO}$	$0.65 V_{CCIO}$	3.6	0.4	$V_{CCIO} - 0.4$	16, 12, 8, 4	-16, -12, -8, -4
					0.2	$V_{CCIO} - 0.2$	0.1	-0.1
LVCMOS15	-0.3	$0.35 V_{CCIO}$	$0.65 V_{CCIO}$	3.6	0.4	$V_{CCIO} - 0.4$	8, 4	-8, -4
					0.2	$V_{CCIO} - 0.2$	0.1	-0.1
LVCMOS12	-0.3	$0.35 V_{CC}$	$0.65 V_{CC}$	3.6	0.4	$V_{CCIO} - 0.4$	6, 2	-6, -2
					0.2	$V_{CCIO} - 0.2$	0.1	-0.1
LVTTTL33	-0.3	0.8	2.0	3.6	0.4	$V_{CCIO} - 0.4$	20, 16, 12, 8, 4	-20, -16, -12, -8, -4
					0.2	$V_{CCIO} - 0.2$	0.1	-0.1
PCI33	-0.3	$0.3 V_{CCIO}$	$0.5 V_{CCIO}$	3.6	$0.1 V_{CCIO}$	$0.9 V_{CCIO}$	1.5	-0.5
SSTL18_I	-0.3	$V_{REF} - 0.125$	$V_{REF} + 0.125$	3.6	0.4	$V_{CCIO} - 0.4$	6.7	-6.7
SSTL18_II (DDR2 Memory)	-0.3	$V_{REF} - 0.125$	$V_{REF} + 0.125$	3.6	0.28	$V_{CCIO} - 0.28$	8	-8
							11	-11
SSTL2_I	-0.3	$V_{REF} - 0.18$	$V_{REF} + 0.18$	3.6	0.54	$V_{CCIO} - 0.62$	7.6	-7.6
							12	-12
SSTL2_II (DDR Memory)	-0.3	$V_{REF} - 0.18$	$V_{REF} + 0.18$	3.6	0.35	$V_{CCIO} - 0.43$	15.2	-15.2
							20	-20
SSTL3_I	-0.3	$V_{REF} - 0.2$	$V_{REF} + 0.2$	3.6	0.7	$V_{CCIO} - 1.1$	8	-8
SSTL3_II	-0.3	$V_{REF} - 0.2$	$V_{REF} + 0.2$	3.6	0.5	$V_{CCIO} - 0.9$	16	-16
SSTL15 (DDR3 Memory)	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	0.3	$V_{CCIO} - 0.3$	7.5	-7.5
						$V_{CCIO} * 0.8$	9	-9
HSTL15_I	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	0.4	$V_{CCIO} - 0.4$	4	-4
							8	-8
HSTL18_I	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	0.4	$V_{CCIO} - 0.4$	8	-8
							12	-12
HSTL18_II	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	0.4	$V_{CCIO} - 0.4$	16	-16

1. For electromigration, the average DC current drawn by I/O pads between two consecutive  $V_{CCIO}$  or GND pad connections, or between the last  $V_{CCIO}$  or GND in an I/O bank and the end of an I/O bank, as shown in the Logic Signal Connections table (also shown as I/O grouping) shall not exceed  $n * 8$  mA, where n is the number of I/O pads between the two consecutive bank  $V_{CCIO}$  or GND connections or between the last  $V_{CCIO}$  and GND in a bank and the end of a bank. IO Grouping can be found in the Data Sheet Pin Tables, which can also be generated from the Lattice Diamond software.

### LVDS25E

The top and bottom sides of LatticeECP3 devices support LVDS outputs via emulated complementary LVCMOS outputs in conjunction with a parallel resistor across the driver outputs. The scheme shown in Figure 3-1 is one possible solution for point-to-point signals.

Figure 3-1. LVDS25E Output Termination Example

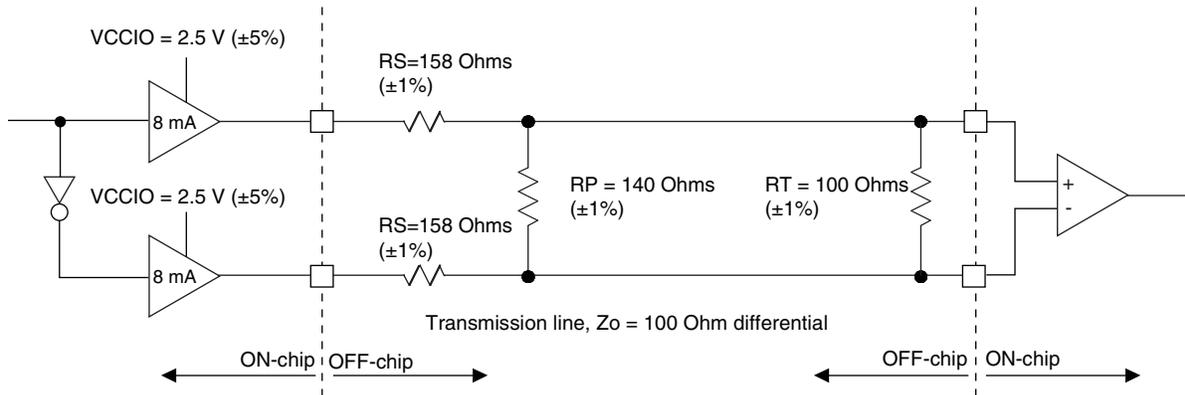


Table 3-1. LVDS25E DC Conditions

Parameter	Description	Typical	Units
V <sub>CCIO</sub>	Output Driver Supply (+/-5%)	2.50	V
Z <sub>OUT</sub>	Driver Impedance	20	Ω
R <sub>S</sub>	Driver Series Resistor (+/-1%)	158	Ω
R <sub>P</sub>	Driver Parallel Resistor (+/-1%)	140	Ω
R <sub>T</sub>	Receiver Termination (+/-1%)	100	Ω
V <sub>OH</sub>	Output High Voltage	1.43	V
V <sub>OL</sub>	Output Low Voltage	1.07	V
V <sub>OD</sub>	Output Differential Voltage	0.35	V
V <sub>CM</sub>	Output Common Mode Voltage	1.25	V
Z <sub>BACK</sub>	Back Impedance	100.5	Ω
I <sub>DC</sub>	DC Output Current	6.03	mA

### LVCMOS33D

All I/O banks support emulated differential I/O using the LVCMOS33D I/O type. This option, along with the external resistor network, provides the system designer the flexibility to place differential outputs on an I/O bank with 3.3 V V<sub>CCIO</sub>. The default drive current for LVCMOS33D output is 12 mA with the option to change the device strength to 4 mA, 8 mA, 16 mA or 20 mA. Follow the LVCMOS33 specifications for the DC characteristics of the LVCMOS33D.

Figure 3-6. Generic DDRX1/DDR2 (With Clock and Data Edges Aligned)

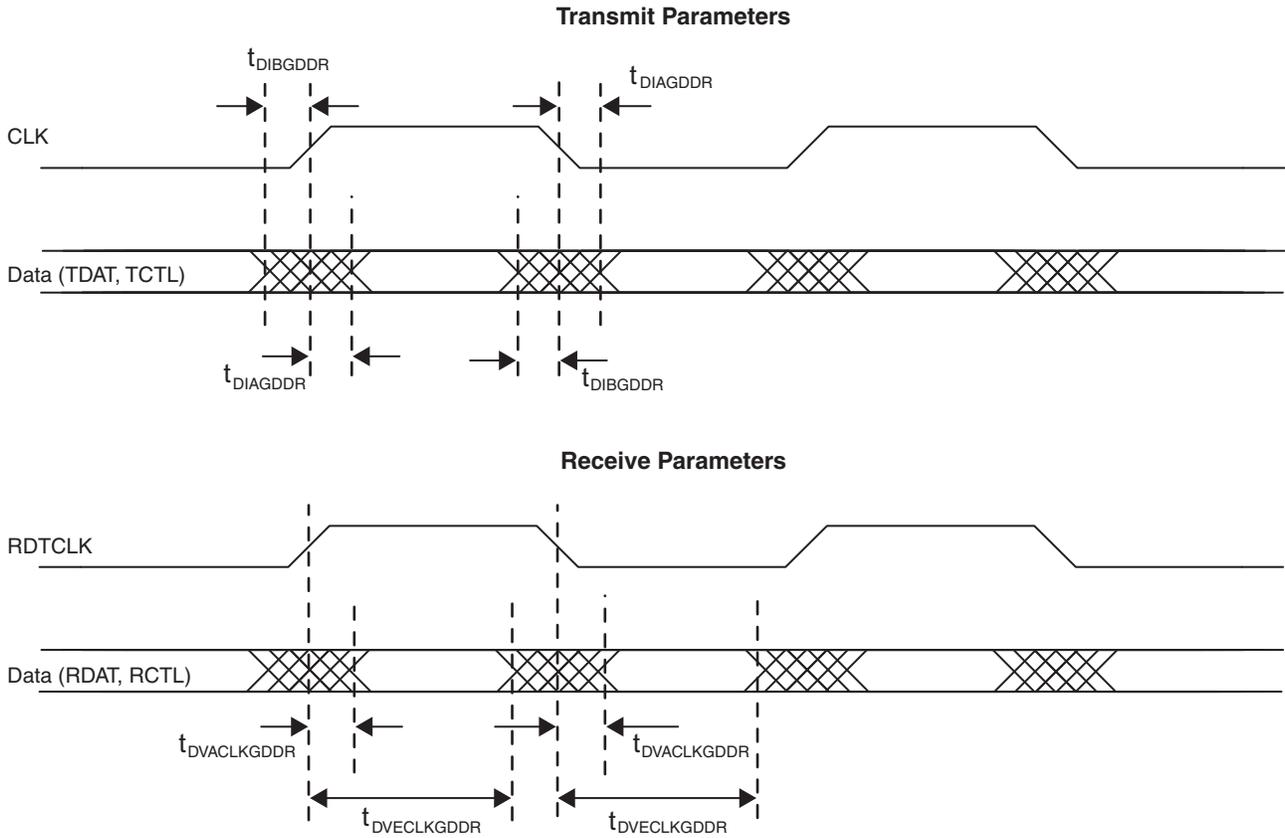


Figure 3-7. DDR/DDR2/DDR3 Parameters

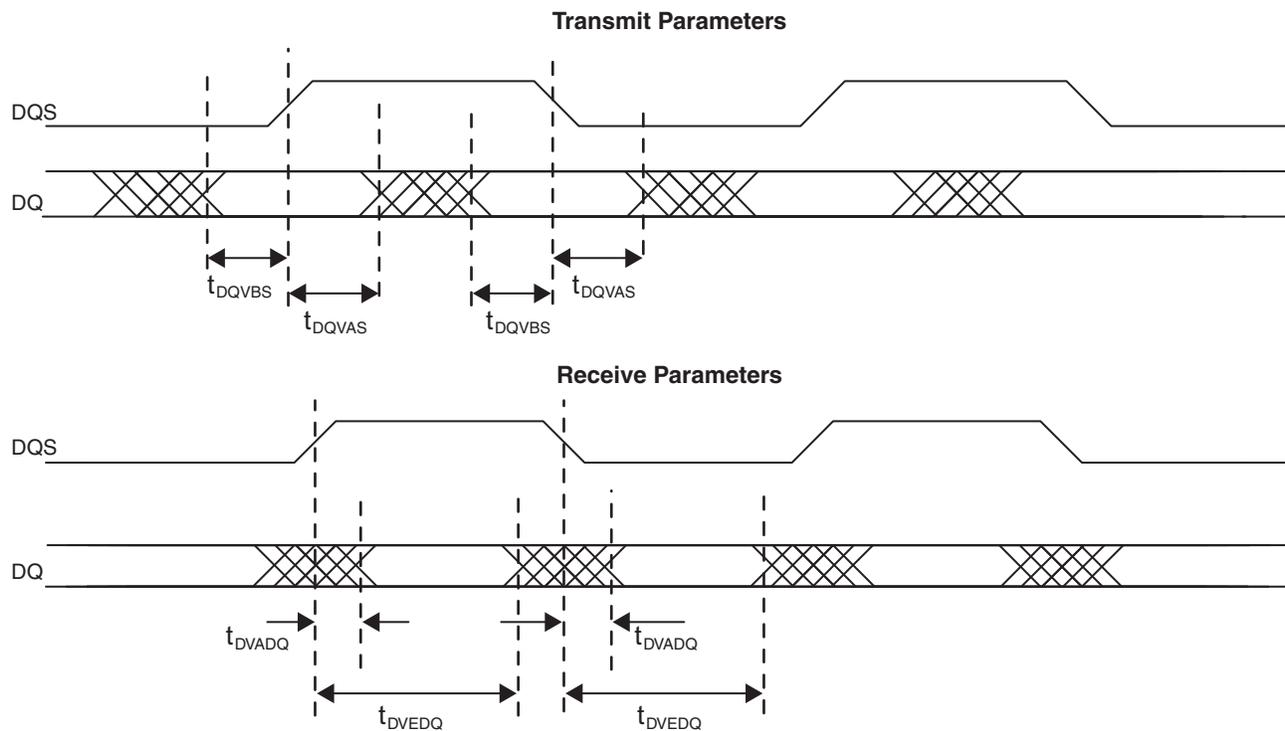
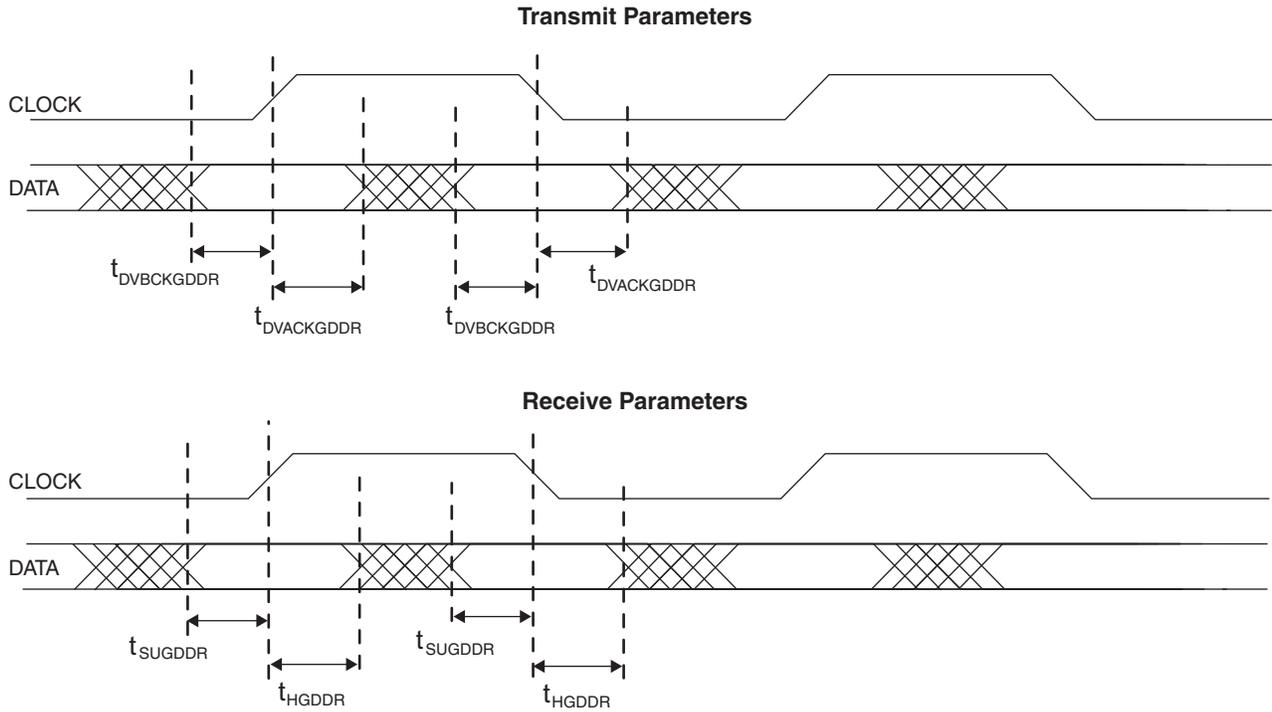


Figure 3-8. Generic DDRX1/DDR2 (With Clock Center on Data Window)



**LatticeECP3 Family Timing Adders<sup>1, 2, 3, 4, 5, 7</sup> (Continued)**
**Over Recommended Commercial Operating Conditions**

Buffer Type	Description	-8	-7	-6	Units
LVC MOS15_4mA	LVC MOS 1.5 4 mA drive, fast slew rate	0.21	0.25	0.29	ns
LVC MOS15_8mA	LVC MOS 1.5 8 mA drive, fast slew rate	0.05	0.07	0.09	ns
LVC MOS12_2mA	LVC MOS 1.2 2 mA drive, fast slew rate	0.43	0.51	0.59	ns
LVC MOS12_6mA	LVC MOS 1.2 6 mA drive, fast slew rate	0.23	0.28	0.33	ns
LVC MOS33_4mA	LVC MOS 3.3 4 mA drive, slow slew rate	1.44	1.58	1.72	ns
LVC MOS33_8mA	LVC MOS 3.3 8 mA drive, slow slew rate	0.98	1.10	1.22	ns
LVC MOS33_12mA	LVC MOS 3.3 12 mA drive, slow slew rate	0.67	0.77	0.86	ns
LVC MOS33_16mA	LVC MOS 3.3 16 mA drive, slow slew rate	0.97	1.09	1.21	ns
LVC MOS33_20mA	LVC MOS 3.3 20 mA drive, slow slew rate	0.67	0.76	0.85	ns
LVC MOS25_4mA	LVC MOS 2.5 4 mA drive, slow slew rate	1.48	1.63	1.78	ns
LVC MOS25_8mA	LVC MOS 2.5 8 mA drive, slow slew rate	1.02	1.14	1.27	ns
LVC MOS25_12mA	LVC MOS 2.5 12 mA drive, slow slew rate	0.74	0.84	0.94	ns
LVC MOS25_16mA	LVC MOS 2.5 16 mA drive, slow slew rate	1.02	1.14	1.26	ns
LVC MOS25_20mA	LVC MOS 2.5 20 mA drive, slow slew rate	0.74	0.83	0.93	ns
LVC MOS18_4mA	LVC MOS 1.8 4 mA drive, slow slew rate	1.60	1.77	1.93	ns
LVC MOS18_8mA	LVC MOS 1.8 8 mA drive, slow slew rate	1.11	1.25	1.38	ns
LVC MOS18_12mA	LVC MOS 1.8 12 mA drive, slow slew rate	0.87	0.98	1.09	ns
LVC MOS18_16mA	LVC MOS 1.8 16 mA drive, slow slew rate	0.86	0.97	1.07	ns
LVC MOS15_4mA	LVC MOS 1.5 4 mA drive, slow slew rate	1.71	1.89	2.08	ns
LVC MOS15_8mA	LVC MOS 1.5 8 mA drive, slow slew rate	1.20	1.34	1.48	ns
LVC MOS12_2mA	LVC MOS 1.2 2 mA drive, slow slew rate	1.37	1.56	1.74	ns
LVC MOS12_6mA	LVC MOS 1.2 6 mA drive, slow slew rate	1.11	1.27	1.43	ns
PCI33	PCI, VCCIO = 3.3 V	-0.12	-0.13	-0.14	ns

1. Timing adders are characterized but not tested on every device.
2. LVC MOS timing measured with the load specified in Switching Test Condition table.
3. All other standards tested according to the appropriate specifications.
4. Not all I/O standards and drive strengths are supported for all banks. See the Architecture section of this data sheet for details.
5. Commercial timing numbers are shown. Industrial numbers are typically slower and can be extracted from the Diamond or ispLEVER software.
6. This data does not apply to the LatticeECP3-17EA device.
7. For details on -9 speed grade devices, please contact your Lattice Sales Representative.

## XAUI/Serial Rapid I/O Type 3/CPRI LV E.30 Electrical and Timing Characteristics

### AC and DC Characteristics

**Table 3-13. Transmit**

**Over Recommended Operating Conditions**

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
$T_{RF}$	Differential rise/fall time	20%-80%	—	80	—	ps
$Z_{TX\_DIFF\_DC}$	Differential impedance		80	100	120	Ohms
$J_{TX\_DDJ}^{2,3,4}$	Output data deterministic jitter		—	—	0.17	UI
$J_{TX\_TJ}^{1,2,3,4}$	Total output data jitter		—	—	0.35	UI

1. Total jitter includes both deterministic jitter and random jitter.
2. Jitter values are measured with each CML output AC coupled into a 50-Ohm impedance (100-Ohm differential impedance).
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.
4. Values are measured at 2.5 Gbps.

**Table 3-14. Receive and Jitter Tolerance**

**Over Recommended Operating Conditions**

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
$RL_{RX\_DIFF}$	Differential return loss	From 100 MHz to 3.125 GHz	10	—	—	dB
$RL_{RX\_CM}$	Common mode return loss	From 100 MHz to 3.125 GHz	6	—	—	dB
$Z_{RX\_DIFF}$	Differential termination resistance		80	100	120	Ohms
$J_{RX\_DJ}^{1,2,3}$	Deterministic jitter tolerance (peak-to-peak)		—	—	0.37	UI
$J_{RX\_RJ}^{1,2,3}$	Random jitter tolerance (peak-to-peak)		—	—	0.18	UI
$J_{RX\_SJ}^{1,2,3}$	Sinusoidal jitter tolerance (peak-to-peak)		—	—	0.10	UI
$J_{RX\_TJ}^{1,2,3}$	Total jitter tolerance (peak-to-peak)		—	—	0.65	UI
$T_{RX\_EYE}$	Receiver eye opening		0.35	—	—	UI

1. Total jitter includes deterministic jitter, random jitter and sinusoidal jitter. The sinusoidal jitter tolerance mask is shown in Figure 3-18.
2. Jitter values are measured with each high-speed input AC coupled into a 50-Ohm impedance.
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.
4. Jitter tolerance parameters are characterized when Full Rx Equalization is enabled.
5. Values are measured at 2.5 Gbps.

## HDMI (High-Definition Multimedia Interface) Electrical and Timing Characteristics

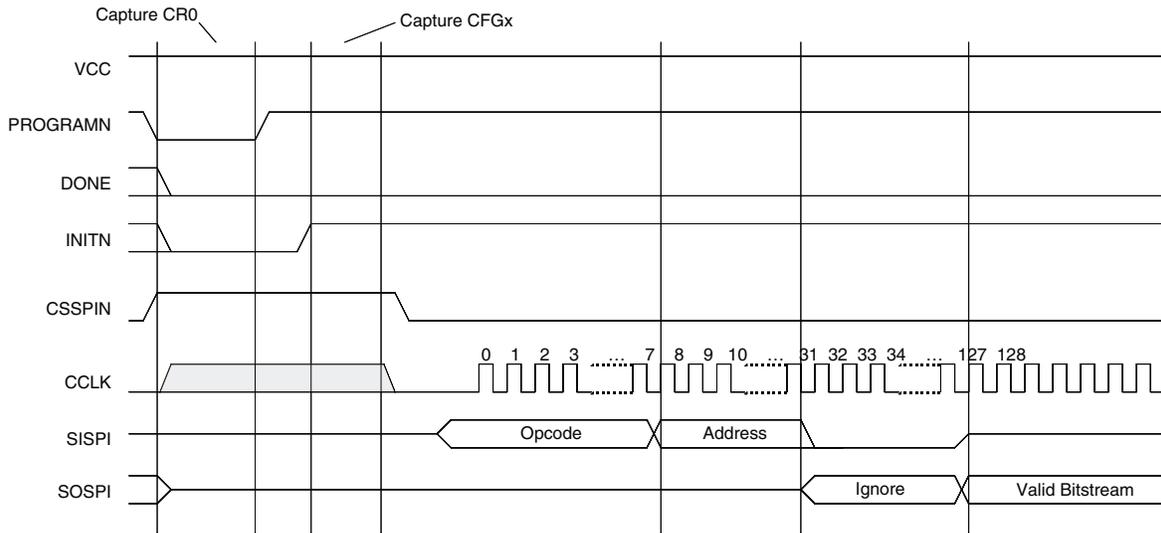
### AC and DC Characteristics

Table 3-22. Transmit and Receive<sup>1,2</sup>

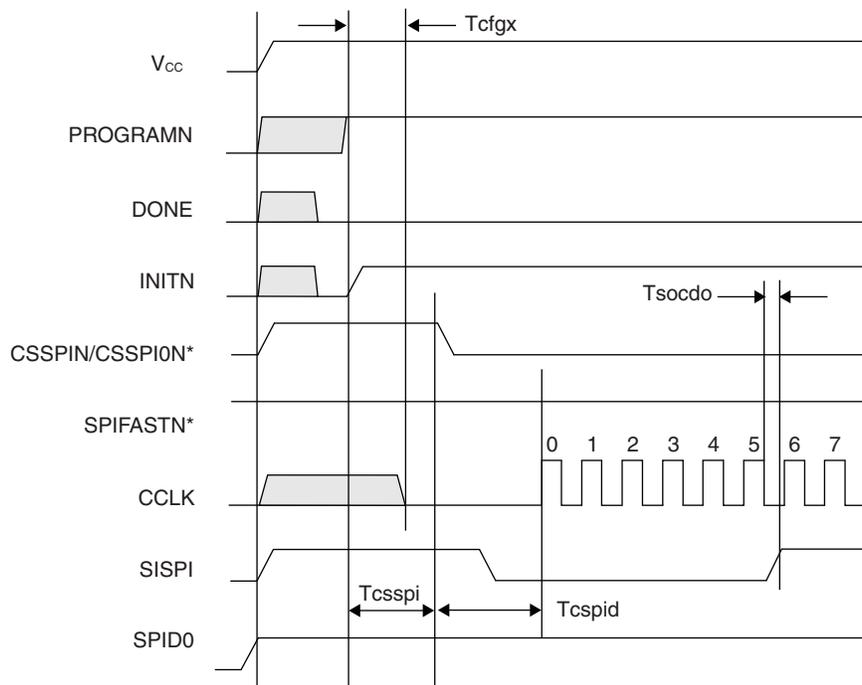
Symbol	Description	Spec. Compliance		Units
		Min. Spec.	Max. Spec.	
<b>Transmit</b>				
Intra-pair Skew		—	75	ps
Inter-pair Skew		—	800	ps
TMDS Differential Clock Jitter		—	0.25	UI
<b>Receive</b>				
$R_T$	Termination Resistance	40	60	Ohms
$V_{ICM}$	Input AC Common Mode Voltage (50-Ohm Setting)	—	50	mV
TMDS Clock Jitter	Clock Jitter Tolerance	—	0.25	UI

1. Output buffers must drive a translation device. Max. speed is 2 Gbps. If translation device does not modify rise/fall time, the maximum speed is 1.5 Gbps.
2. Input buffers must be AC coupled in order to support the 3.3 V common mode. Generally, HDMI inputs are terminated by an external cable equalizer before data/clock is forwarded to the LatticeECP3 device.

**Figure 3-28. Master SPI Configuration Waveforms**



**Figure 3-29. Master SPI POR Waveforms**

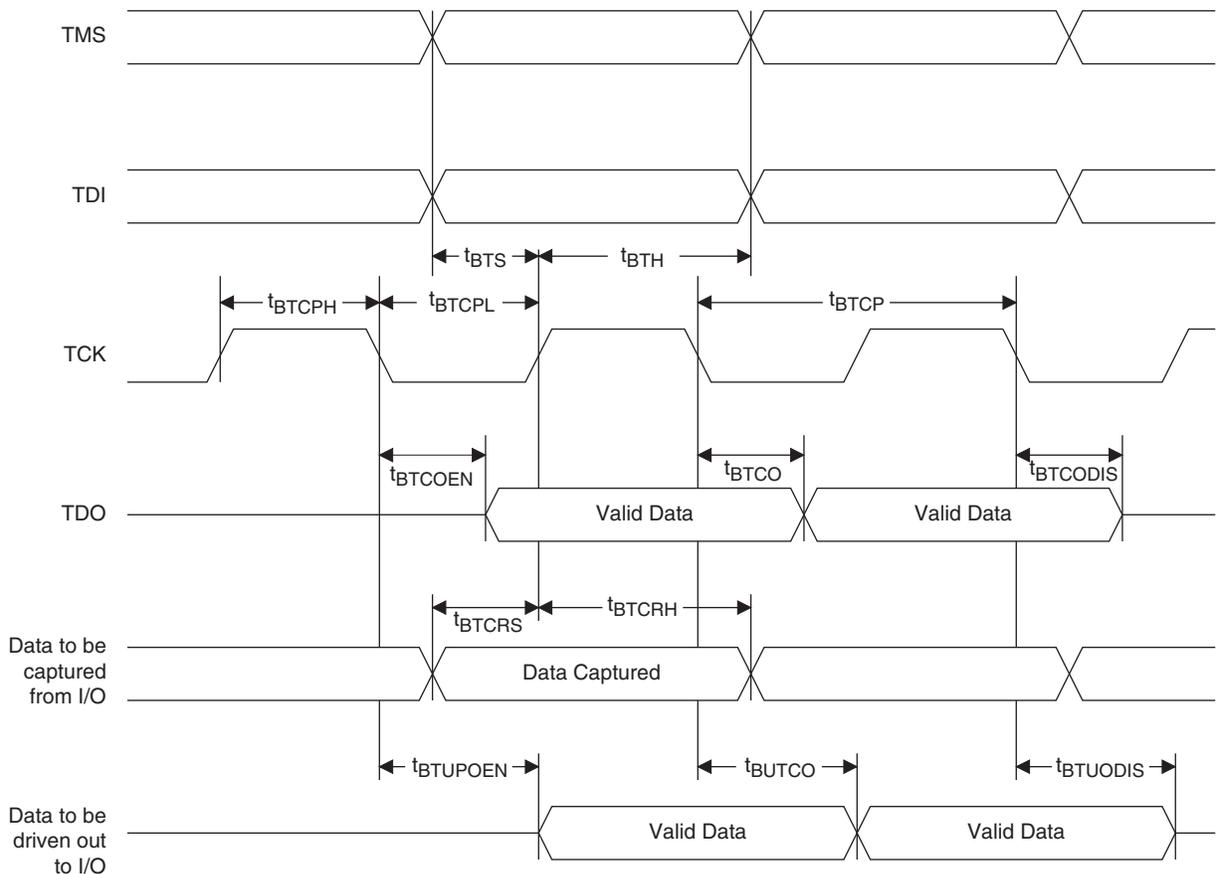


## JTAG Port Timing Specifications

Over Recommended Operating Conditions

Symbol	Parameter	Min	Max	Units
$f_{MAX}$	TCK clock frequency	—	25	MHz
$t_{BTCP}$	TCK [BSCAN] clock pulse width	40	—	ns
$t_{BTCPH}$	TCK [BSCAN] clock pulse width high	20	—	ns
$t_{BTCPL}$	TCK [BSCAN] clock pulse width low	20	—	ns
$t_{BTS}$	TCK [BSCAN] setup time	10	—	ns
$t_{BTH}$	TCK [BSCAN] hold time	8	—	ns
$t_{BTRF}$	TCK [BSCAN] rise/fall time	50	—	mV/ns
$t_{BTCO}$	TAP controller falling edge of clock to valid output	—	10	ns
$t_{BTCODIS}$	TAP controller falling edge of clock to valid disable	—	10	ns
$t_{BTCOEN}$	TAP controller falling edge of clock to valid enable	—	10	ns
$t_{BTCRS}$	BSCAN test capture register setup time	8	—	ns
$t_{BTCRH}$	BSCAN test capture register hold time	25	—	ns
$t_{BUTCO}$	BSCAN test update register, falling edge of clock to valid output	—	25	ns
$t_{BTUODIS}$	BSCAN test update register, falling edge of clock to valid disable	—	25	ns
$t_{BTUPOEN}$	BSCAN test update register, falling edge of clock to valid enable	—	25	ns

Figure 3-32. JTAG Port Timing Waveforms



**Point-to-Point LVDS (PPLVDS)**
**Over Recommended Operating Conditions**

Description	Min.	Typ.	Max.	Units
Output driver supply (+/- 5%)	3.14	3.3	3.47	V
	2.25	2.5	2.75	V
Input differential voltage	100	—	400	mV
Input common mode voltage	0.2	—	2.3	V
Output differential voltage	130	—	400	mV
Output common mode voltage	0.5	0.8	1.4	V

**RSDS**
**Over Recommended Operating Conditions**

Parameter Symbol	Description	Min.	Typ.	Max.	Units
$V_{OD}$	Output voltage, differential, $R_T = 100$ Ohms	100	200	600	mV
$V_{OS}$	Output voltage, common mode	0.5	1.2	1.5	V
$I_{RSDS}$	Differential driver output current	1	2	6	mA
$V_{THD}$	Input voltage differential	100	—	—	mV
$V_{CM}$	Input common mode voltage	0.3	—	1.5	V
$T_R, T_F$	Output rise and fall times, 20% to 80%	—	500	—	ps
$T_{ODUTY}$	Output clock duty cycle	35	50	65	%

Note: Data is for 2 mA drive. Other differential driver current options are available.

**Pin Information Summary (Cont.)**

Pin Information Summary		ECP3-70EA		
Pin Type		484 fpBGA	672 fpBGA	1156 fpBGA
Emulated Differential I/O per Bank	Bank 0	21	30	43
	Bank 1	18	24	39
	Bank 2	8	12	13
	Bank 3	20	23	33
	Bank 6	22	25	33
	Bank 7	11	16	18
	Bank 8	12	12	12
High-Speed Differential I/O per Bank	Bank 0	0	0	0
	Bank 1	0	0	0
	Bank 2	6	9	9
	Bank 3	9	12	16
	Bank 6	11	14	16
	Bank 7	9	12	13
	Bank 8	0	0	0
Total Single-Ended/ Total Differential I/O per Bank	Bank 0	42/21	60/30	86/43
	Bank 1	36/18	48/24	78/39
	Bank 2	28/14	42/21	44/22
	Bank 3	58/29	71/35	98/49
	Bank 6	67/33	78/39	98/49
	Bank 7	40/20	56/28	62/31
	Bank 8	24/12	24/12	24/12
DDR Groups Bonded per Bank <sup>1</sup>	Bank 0	3	5	7
	Bank 1	3	4	7
	Bank 2	2	3	3
	Bank 3	3	4	5
	Bank 6	4	4	5
	Bank 7	3	4	4
	Configuration Bank 8	0	0	0
SERDES Quads		1	2	3

1. Some DQS groups may not support DQS-12. Refer to the device pinout (.csv) file.

Part Number	Voltage	Grade <sup>1</sup>	Power	Package	Pins	Temp.	LUTs (K)
LFE3-150EA-6FN672C	1.2 V	-6	STD	Lead-Free fpBGA	672	COM	149
LFE3-150EA-7FN672C	1.2 V	-7	STD	Lead-Free fpBGA	672	COM	149
LFE3-150EA-8FN672C	1.2 V	-8	STD	Lead-Free fpBGA	672	COM	149
LFE3-150EA-6LFN672C	1.2 V	-6	LOW	Lead-Free fpBGA	672	COM	149
LFE3-150EA-7LFN672C	1.2 V	-7	LOW	Lead-Free fpBGA	672	COM	149
LFE3-150EA-8LFN672C	1.2 V	-8	LOW	Lead-Free fpBGA	672	COM	149
LFE3-150EA-6FN1156C	1.2 V	-6	STD	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-7FN1156C	1.2 V	-7	STD	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-8FN1156C	1.2 V	-8	STD	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-6LFN1156C	1.2 V	-6	LOW	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-7LFN1156C	1.2 V	-7	LOW	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-8LFN1156C	1.2 V	-8	LOW	Lead-Free fpBGA	1156	COM	149

1. For ordering information on -9 speed grade devices, please contact your Lattice Sales Representative.

Part Number	Voltage	Grade	Power	Package	Pins	Temp.	LUTs (K)
LFE3-150EA-6FN672CTW <sup>1</sup>	1.2 V	-6	STD	Lead-Free fpBGA	672	COM	149
LFE3-150EA-7FN672CTW <sup>1</sup>	1.2 V	-7	STD	Lead-Free fpBGA	672	COM	149
LFE3-150EA-8FN672CTW <sup>1</sup>	1.2 V	-8	STD	Lead-Free fpBGA	672	COM	149
LFE3-150EA-6FN1156CTW <sup>1</sup>	1.2 V	-6	STD	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-7FN1156CTW <sup>1</sup>	1.2 V	-7	STD	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-8FN1156CTW <sup>1</sup>	1.2 V	-8	STD	Lead-Free fpBGA	1156	COM	149

1. Note: Specifications for the LFE3-150EA-*spFNpkgCTW* and LFE3-150EA-*spFNpkgITW* devices, (where *sp* is the speed and *pkg* is the package), are the same as the LFE3-150EA-*spFNpkgC* and LFE3-150EA-*spFNpkgI* devices respectively, except as specified below.

- The CTC (Clock Tolerance Circuit) inside the SERDES hard PCS in the TW device is not functional but it can be bypassed and implemented in soft IP.
- The SERDES XRES pin on the TW device passes CDM testing at 250 V.

## For Further Information

A variety of technical notes for the LatticeECP3 family are available on the Lattice website at [www.latticesemi.com](http://www.latticesemi.com).

- TN1169, [LatticeECP3 sysCONFIG Usage Guide](#)
- TN1176, [LatticeECP3 SERDES/PCS Usage Guide](#)
- TN1177, [LatticeECP3 sysIO Usage Guide](#)
- TN1178, [LatticeECP3 sysCLOCK PLL/DLL Design and Usage Guide](#)
- TN1179, [LatticeECP3 Memory Usage Guide](#)
- TN1180, [LatticeECP3 High-Speed I/O Interface](#)
- TN1181, [Power Consumption and Management for LatticeECP3 Devices](#)
- TN1182, [LatticeECP3 sysDSP Usage Guide](#)
- TN1184, [LatticeECP3 Soft Error Detection \(SED\) Usage Guide](#)
- TN1189, [LatticeECP3 Hardware Checklist](#)
- TN1215, [LatticeECP2MS and LatticeECP2S Devices](#)
- TN1216, [LatticeECP2/M and LatticeECP3 Dual Boot Feature Advanced Security Encryption Key Programming Guide for LatticeECP3](#)
- TN1222, [LatticeECP3 Slave SPI Port User's Guide](#)

For further information on interface standards refer to the following websites:

- JEDEC Standards (LVTTTL, LVCMOS, SSTL, HSTL): [www.jedec.org](http://www.jedec.org)
- PCI: [www.pcisig.com](http://www.pcisig.com)